IGBT Power Module
1200V / 150A

Preliminary

HD-9434

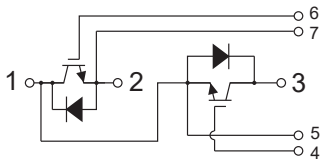
Features

- 34mm Fast Switching Trench / Field Stop IGBT Technology
- Low Switching Losses
- Super Fast Diodes
- High Short Circuit Capability

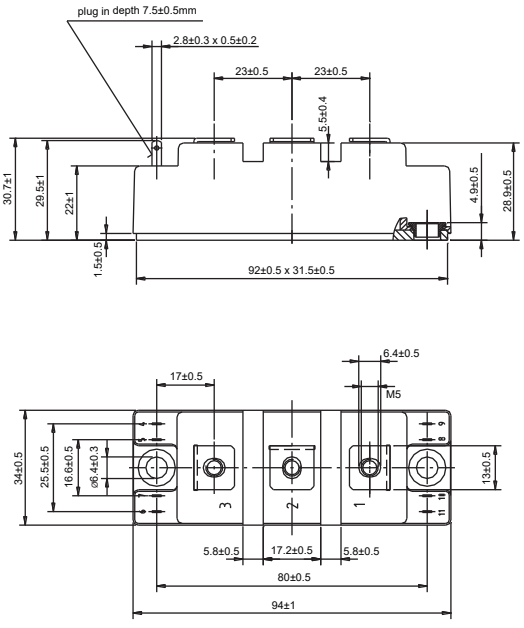
Applications

- Welder / Power Supply
- UPS / Inverter
- Industrial Motor Drive

Circuit Diagram Headline



Package Outlines



Dimensions in mm (1 mm = 0.0394")

Maximum Ratings (T_C= 25℃)

Item		Symbol	Rated Value	Unit
Collector-Emitter Voltage	T_{VJ} = 25℃	V_{CES}	1200	V
Gate-Emitter Peak Voltage		V_{GES}	±20	V
Continuous DC Collector Current	T_C = 100℃	$I_{C,nom.}$	150	A
Repetitive Peak Collector Current	tp =1ms	I_{CRM}	300	A
Total Power Dissipation		P_{tot}	790	W
Isolation Voltage	RMS, f=50Hz, t=1min	V_{iso}	3000	V
Continuous DC Forward Current		I_F	150	A
Repetitive Peak Forward Current	tp =1ms	I_{FRM}	300	A
Temperature under switching conditions		$T_{VJ\ op}$	−40～+150	℃
Storage Temperature		T_{stg}	−40～+125	℃
Mounting Torque	Module Base to Heatsink (M6)		3～5	N.m
	Busbar to Terminal (M5)		2.5～5	

■ Electrical Characteristics (T_{VJ} = 25℃)

Characteristics	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Collector-emitter saturation voltage	$V_{CE\ sat}$	I_C =150A, V_{GE} =15V	T_{vj}=25℃		1.75	2.15	V
		I_C =150A, V_{GE} =15V	T_{vj}=125℃		2.05		
		I_C =150A, V_{GE} =15V	T_{vj}=150℃		2.1		
Gate threshold voltage	V_{GEth}	I_C =5.3mA, V_{CE} =V_{GE}, T_{vj} =25℃		5.8	6.4	6.9	V
Gate charge	Q_G	V_{GE}= -15 V... +15 V			1.7		µC
Internal gate resistor	R_{Gint}	T_{vj} =25℃			1		Ω
Input capacitance	C_{ies}	f = 1MHz, T_{vj} =25℃, V_{CE} =25V, V_{GE} =0V			26.438		nF
Output capacitance	C_{oes}	f = 1MHz, T_{vj} =25℃, V_{CE} =25V, V_{GE} =0V			0.653		nF
Reverse transfer capacitance	C_{res}	f = 1MHz, T_{vj} =25℃, V_{CE} =25V, V_{GE} =0V			0.382		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} =1200V, V_{GE} =0V, T_{vj} =25℃				1	mA
Gate-emitter leakage current	I_{GES}	V_{CE} =0V, V_{GE} =20V, T_{vj} =25℃				100	nA
Turn-on delay time, inductive load	$t_{d\ on}$	I_C =150A, V_{CE} =600V	T_{vj}=25℃		0.144		µs
		V_{GE} = ±15V	T_{vj}=125℃		0.149		
		R_{Gon} =1.1Ω	T_{vj}=150℃		0.27		
Rise time, inductive load	t_r	I_C =150A, V_{CE} =600V	T_{vj}=25℃		0.05		µs
		V_{GE} = ±15V	T_{vj}=125℃		0.054		
		R_{Gon} =1.1Ω	T_{vj}=150℃		0.06		
Turn-off delay time, inductive load	$t_{d\ off}$	I_C =150A, V_{CE} =600V	T_{vj}=25℃		0.274		µs
		V_{GE} = ±15V	T_{vj}=125℃		0.296		
		R_{Goff} =1.1Ω	T_{vj}=150℃		0.5		
Fall time, inductive load	t_f	I_C =150A, V_{CE} =600V	T_{vj}=25℃		0.102		µs
		V_{GE} = ±15V	T_{vj}=125℃		0.17		
		R_{Goff} =1.1Ω	T_{vj}=150℃		0.21		
Turn-on energy loss per pulse	E_{on}	I_C =150A, V_{CE} =600V, L_S =30nH	T_{vj}=25℃		4.02		mJ
		V_{GE} = ±15V, di/dt =3400A/µs (T_{vj} =150℃)	T_{vj}=125℃		7.85		
		R_{Gon} =1.1Ω	T_{vj}=150℃		10.80		
Turn-off energy loss per pulse	E_{off}	I_C =150A, V_{CE} =600V, L_S =30nH	T_{vj}=25℃		11.67		mJ
		V_{GE} = ±15V, du/dt =3300V/µs (T_{vj} =150℃)	T_{vj}=125℃		15.65		
		R_{Goff} =1.1Ω	T_{vj}=150℃		17.65		
SC data	I_{SC}	V_{GE} ≤15V, V_{CC} =800V	t_P ≤10µs,		600		A
		V_{CEmax} =V_{CES} - L_{sCE} ·di/dt	T_{vj}=150℃				
Thermal resistance, junction to case	R_{thJC}	per IGBT				0.19	℃/W
Thermal resistance, case to heatsink	R_{thCH}	per IGBT			0.081		℃/W
External gate resistance	R_{Gext}	T_{vj} =25℃		1.1		10	Ω

■ Diode Ratings & Characteristics

Characteristics	Symbol	Test Conditions	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	T_{vj} =25°C	1200	V
Continuous DC forward current	I_F		150	A
Repetitive peak forward current	I_{FRM}	t_P =1ms	300	A
I^2t - value	I^2t	V_R =0V, t_P =10ms, T_{vj} =125°C	4100	A^2s
		V_R =0V, t_P =10ms, T_{vj} =150°C	4000	

Characteristics	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Forward voltage	V_F	I_F =150A, V_{GE} =0V	T_{vj} =25°C		2	2.5	V
		I_F =150A, V_{GE} =0V	T_{vj} =125°C		1.9		
		I_F =150A, V_{GE} =0V	T_{vj} =150°C		1.85		
Peak reverse recovery current	I_{RM}	I_F =150A, -di$_F$/dt =3400A/µs (T_{vj}=150°C)	T_{vj} =25°C		120		A
		V_R =600V	T_{vj} =125°C		170		
		V_{GE} = -15V	T_{vj} =150°C		180		
Recovered charge	Qr	I_F =150A, -di$_F$/dt =3400A/µs (T_{vj}=150°C)	T_{vj} =25°C		9.08		µC
		V_R =600V	T_{vj} =125°C		20.0		
		V_{GE} = -15V	T_{vj} =150°C		23.9		
Reverse recovery energy	Erec	I_F =150A, -di$_F$/dt =3400A/µs (T_{vj}=150°C)	T_{vj} =25°C		7.68		mJ
		V_R =600V	T_{vj} =125°C		13.29		
		V_{GE} = -15V	T_{vj} =150°C		15.0		
Reverse Recovery Time	Trr	I_F =150A, -di$_F$/dt =3400A/µs, V_R =600V, V_{GE} = -15V, T_{vj}=25°C			88		ns
Thermal resistance, junction to case	R_{thJC}	per diode				0.31	°C/W
Thermal resistance, case to heatsink	R_{thCH}	per diode			0.13		°C/W
Temperature under switching conditions	$T_{vj\ op}$			-40		150	°C

■ Module Ratings & Characteristics

Characteristics	Symbol	Test Conditions	Value	Unit
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance		terminal to heatsink	17	mm
		terminal to terminal	20	
Clearance		terminal to heatsink	17	mm
		terminal to terminal	9.5	
Comperative tracking index	CTI		>200	

Typical Characteristics

Preliminary Data

Fig.1 Output characteristic IGBT,Inverter (typical)

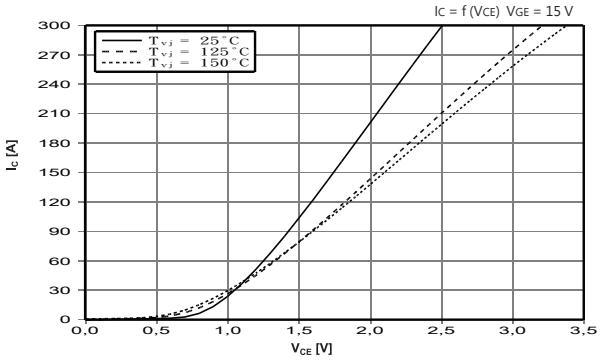


Fig.2 Output characteristic IGBT,Inverter (typical)

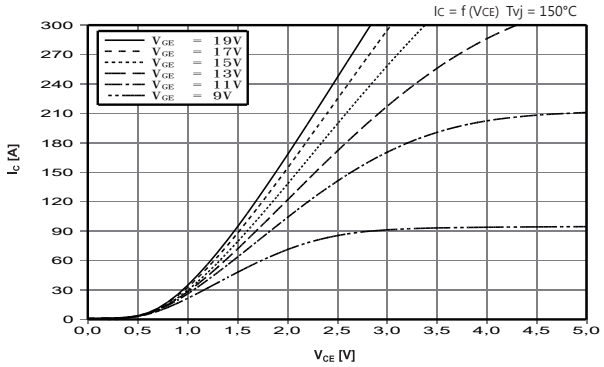


Fig.3 Transfer characteristic IGBT,Inverter (typical)

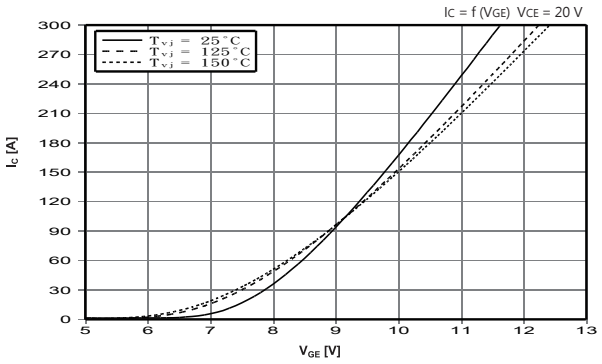


Fig.4 Switching losses IGBT,Inverter (typical)

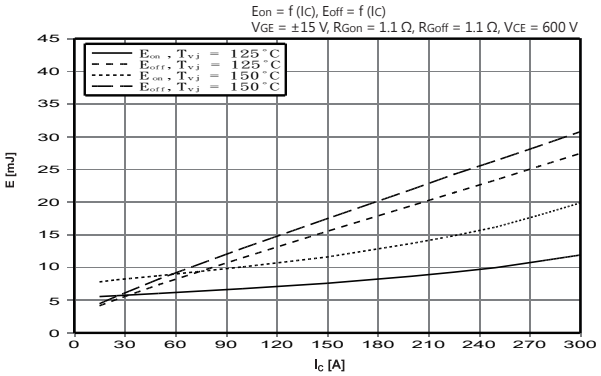


Fig.5 Switching losses IGBT,Inverter (typical)

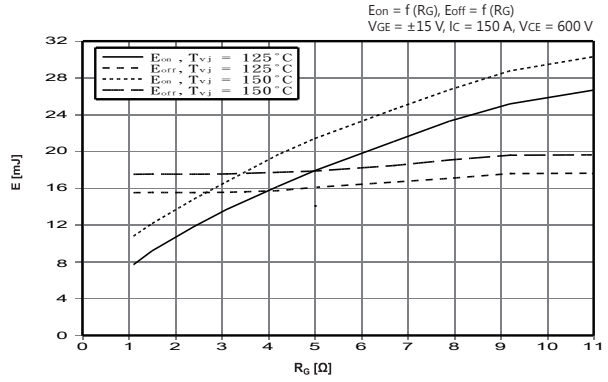


Fig.6 Transient thermal impedance IGBT,Inverter

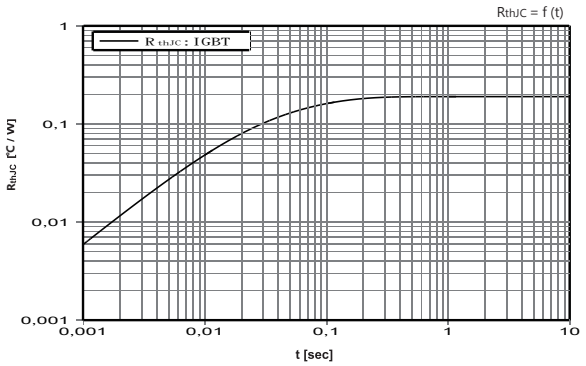


Fig.7 Reverse bias safe operating area IGBT,Inverter (RBSOA)

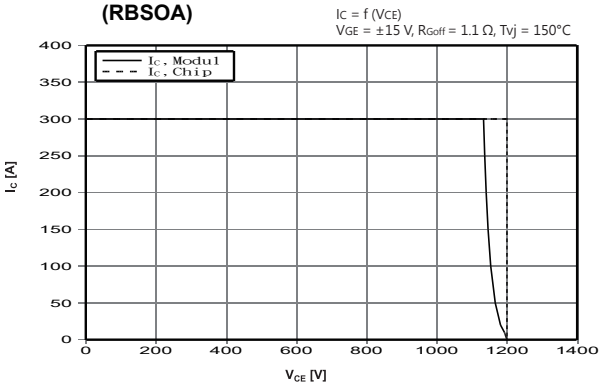
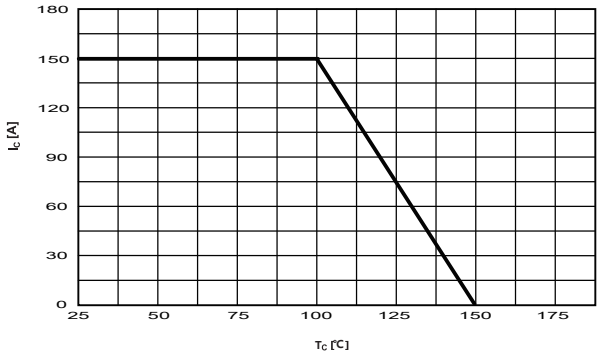


Fig.8 Output characteristic IGBT,Inverter (typical)



Typical Characteristics

Preliminary Data

Fig.9 Switching losses Diode, Inverter (typical)

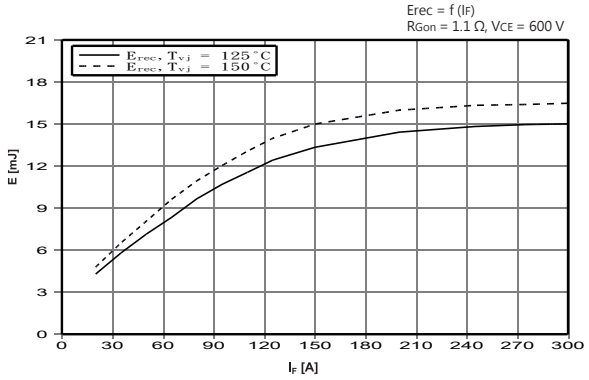


Fig.10 Switching losses Diode, Inverter (typical)

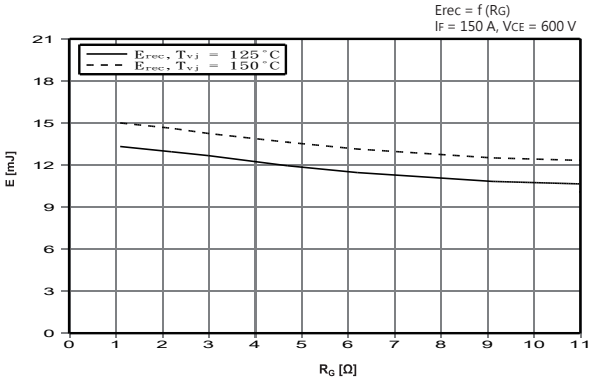


Fig.11 Transient thermal impedance Diode, Inverter

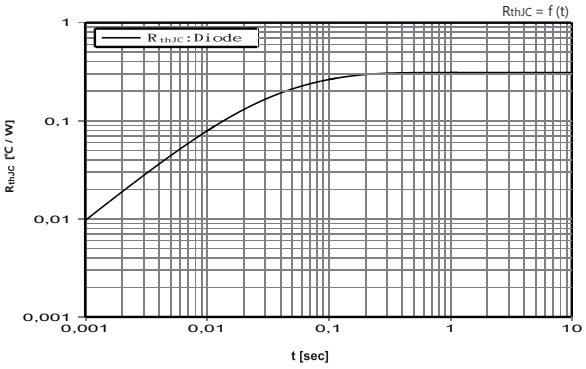
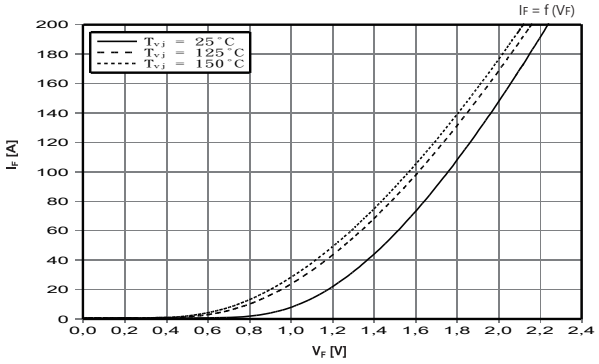


Fig.12 Forward characteristic of Diode, Inverter (typical)



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